

STB16NF06L

N-channel 60V - 0.07Ω - 16A - D²PAK STripFET™ Power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STB16NF06L	60V	<0.09Ω	16A

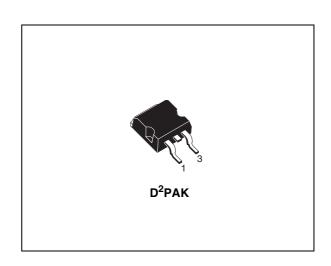
- Exceptional dv/dt capability
- Low gate charge at 100°C
- Logic level device
- Low threshold drive

Description

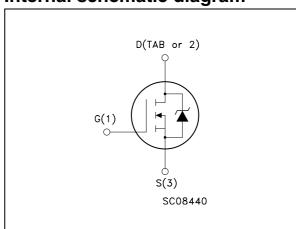
This Power MOSFET is the latest development of STMicroelectronis unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

■ Switching application



Internal schematic diagram



Order codes

Pa	art number	Marking	Package	Packaging	
ST	TB16NF06L	B16NF06L	D ² PAK	Tape & reel	

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STB16NF06L Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	60	V
V _{GS}	Gate- source voltage	± 16	V
I _D	Drain current (continuous) at T _C = 25°C	16	А
I _D	Drain current (continuous) at T _C = 100°C	11	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	64	Α
P _{tot}	Total dissipation at T _C = 25°C	45	W
	Derating Factor	r 0.3 V	
dv/dt ⁽²⁾	Peak diode recovery avalanche energy	23	V/ns
E _{AS} (3)	Single pulse avalanche energy 127		mJ
T _{stg}	Storage temperature	55 to 175	°C
Tj	Max. operating junction temperature	-55 to 175 °C	

^{1.} Pulse width limited by safe operating area.

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	3.33	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W
T _J	T _J Maximum lead temperature for soldering purpose		°C

^{2.} $I_{SD} \leq 6A$, di/dt $\geq 10A/\mu s$, $V_{DD} = V(_{BR)DSS}$, $T_j \leq T_{JMAX}$

^{3.} Starting $T_j = 25$ °C, $I_D = 8A$, $V_{DD} = 30V$

Electrical characteristics STB16NF06L

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1			V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 5V, I_{D} = 8A$ $V_{GS} = 10V, I_{D} = 8A$		0.08 0.07	0.10 0.09	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	$V_{DS}>I_{D(on)} \times R_{DS(on)max},$ $I_D = 80A$		17		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		345 72 29		pF pF pF
$\begin{array}{c} t_{\text{d(on)}} \\ t_{\text{r}} \\ t_{\text{d(off)}} \\ t_{\text{f}} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 30V, I_D = 8A R_G = 4.7 Ω V_{GS} = 4.5V (see <i>Figure 12</i>)		10 37 20 12.5		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 48V, I_{D} = 16A, V_{GS} = 4.5V, R_{G} = 4.7 Ω (see <i>Figure 13</i>)		7.3 2.1 3.1	10	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				16 64	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 16A, V _{GS} = 0			1.3	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 16A$, di/dt = 100A/ μ s, $V_{DD} = 16V$, $T_{j} = 150$ °C (see <i>Figure 14</i>)		50 67.5 2.7		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

Electrical characteristics STB16NF06L

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

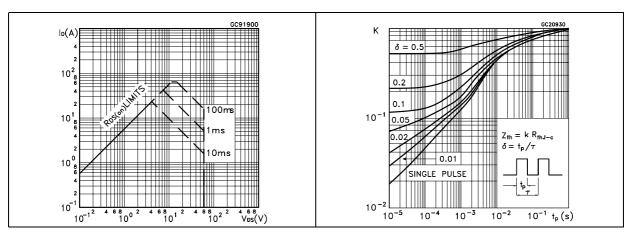


Figure 3. Output characterisics

Figure 4. Transfer characteristics

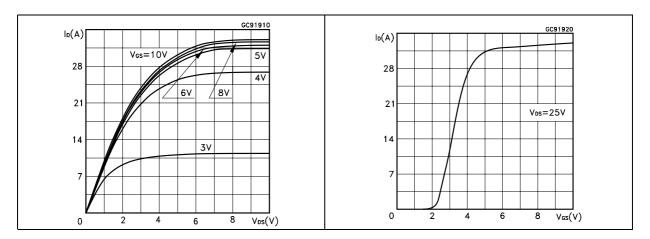
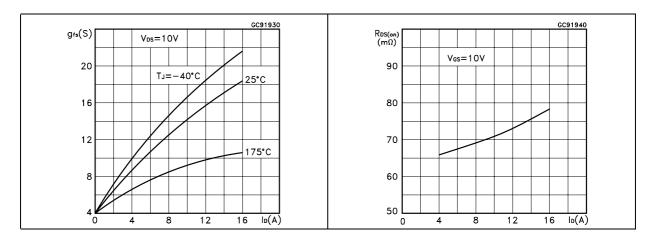


Figure 5. Transconductance

Figure 6. Static drain-source on resistance



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Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

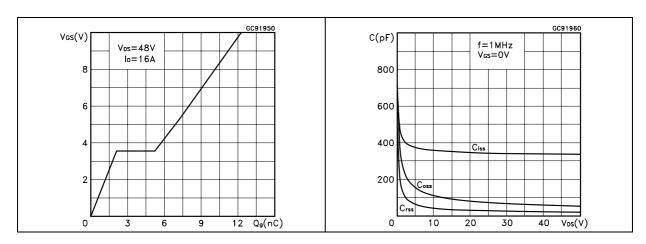


Figure 9. Normalized gate threshold voltage Figure 10. Normalized on resistance vs vs temperature temperature

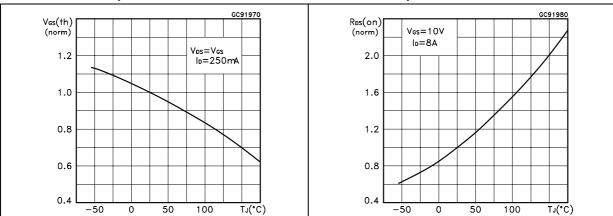
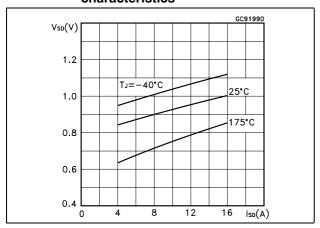


Figure 11. Source-drain diode forward characteristics



Test circuit STB16NF06L

3 Test circuit

Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

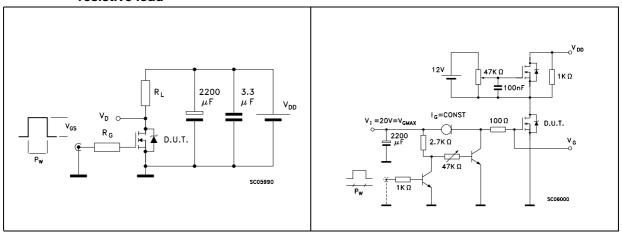


Figure 14. Test circuit for inductive load switching and diode recovery times

Figure 15. Unclamped Inductive load test circuit

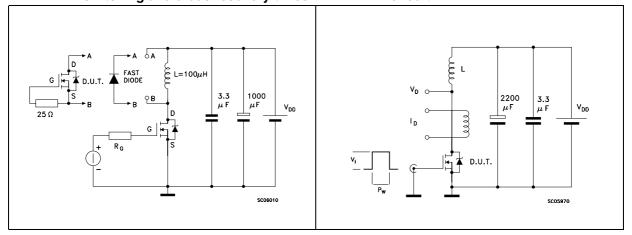
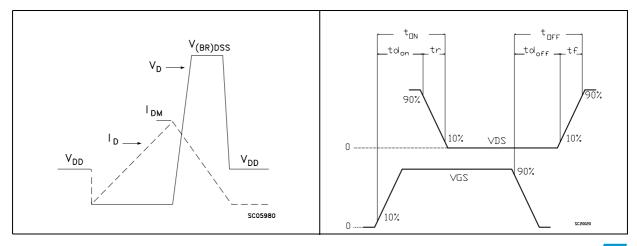


Figure 16. Unclamped inductive waveform

Figure 17. Switching time waveform



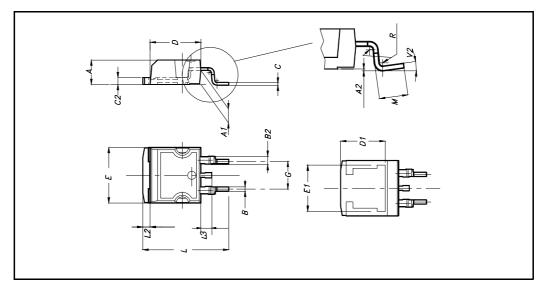
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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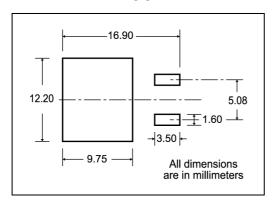
D²PAK MECHANICAL DATA

DIM	mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	O _ō		4º			

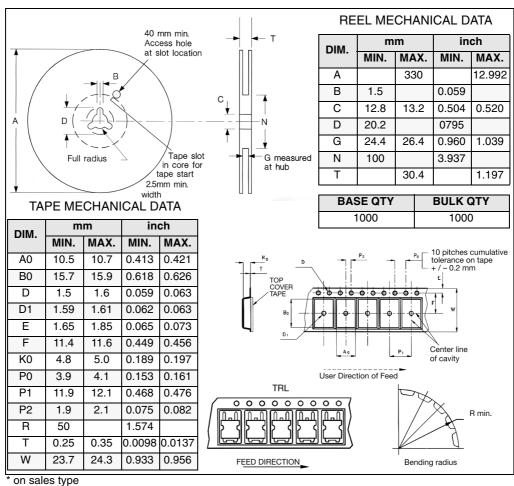


Packing mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



Revision history STB16NF06L

6 Revision history

Table 6. Revision history

Date	Revision	Changes
21-Jun-2004	1	First version
26-Jun-2006	2	New template, no content change

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